

ABSTRACT

A method of removing unwanted edge copper from an edge region of a wafer is provided. The method is applied subsequent to an electrochemical process to deposit a copper layer on a surface of a wafer. The edge region, which has the unwanted edge copper, includes a front edge surface, a back edge surface and a bevel. During the removal as the wafer is rotated, a stream of etchant solution from a front edge nozzle is delivered to the front edge surface of the wafer while another stream is delivered to the back edge surface from a back edge nozzle. Rotational motion of the wafer directs the etchant, which is delivered by the front and back edge nozzles, to the bevel and thereby causing removal of the unwanted copper from the edge region of the wafer.